STATUS OF THE CLAIMS

Claims 1-25 (Canceled).

26. (Previously presented) A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said composition consisting of:

a flowing plasma etchant mixture consisting of at least one fluorocarbon and ammonia, wherein said at least one fluorocarbon and ammonia form a reactive mixture.

27. (Previously presented) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of fluorohydrocarbons, chlorofluorocarbons and chlorofluorohydrocarbons.

28. (Original) The composition of claim 27, wherein said fluorocarbon is at least one member selected from the group consisting of C_4F_8, C_4F_6, C_5F_8, CF_4, C_2F_6, C_3F_8, CHF_3, and CH_2F_2.

29. (Original) The composition of claim 26, wherein said fluorocarbon is at least one member selected from the group consisting of CF_4, CHF_3, and CH_2F_2.

30. (Original) The composition of claim 29, wherein said fluorocarbon is at least two members selected from the group consisting of CF_4, CHF_3, and CH_2F_2.

31. (Original) The composition of claim 30, wherein said fluorocarbon is a combination of CF_4, CHF_3, and CH_2F_2.

32. (Previously presented) The composition of claim 26, wherein said composition is ineffective to remove side wall spacers of a gate stack formed over said substrate.

Claims 33-70 (Canceled).

71. (Previously presented) A composition suitable for use in etching an insulative layer formed on a substrate in a semiconductor device, said composition consisting of:

a plasma etchant mixture consisting of CF_4, at least one other fluorocarbon, and NH_3, wherein said CF_4, at least one other fluorocarbon, and NH_3 form a reactive mixture.

Claims 72-76 (Canceled).

77. (Previously presented) A composition suitable for use in etching an insulative layer formed over a substrate in a semiconductor device, said composition consisting of:

a gaseous etchant mixture consisting of at least one fluorocarbon and ammonia, wherein said at least one fluorocarbon and ammonia form a reactive mixture.